

## 1. Description

The FDC604P is the high cell density trenched P-channel MOSFETs, which provide excellent  $R_{DS(ON)}$  and gate charge for most of the synchronous buck converter applications.

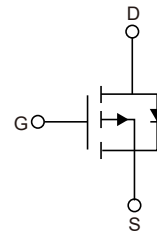
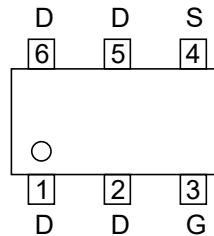
## 2. Features

- $V_{DS(V)} = -20V$
- $I_D = -6A (V_{GS} = 10V)$
- $R_{DS(ON)} < 35m\Omega (V_{GS} = 10V)$
- $R_{DS(ON)} < 53m\Omega (V_{GS} = 4.5V)$

## 3. Pinning information

Pin	Symbol	Description
1,2,5,6	D	DRAIN
3	G	GATE
4	S	SOURCE

SOP-8



## 4. Absolute Maximum Ratings $T_A = 25^\circ C$ unless otherwise noted

Parameter	Symbol	Rating	Units	
Drain Source Voltage	$V_{DS}$	-20	V	
Gate Source Voltage	$V_{GS}$	$\pm 12$	V	
Continuous Drain Current, $V_{GS} = -4.5V$ <sup>1</sup>	$I_D$	$T_A = 25^\circ C$	-6	A
		$T_A = 70^\circ C$	-3	A
Pulsed Drain Current <sup>2</sup>	$I_{DM}$	-16	A	
Total Power Dissipation <sup>3</sup>	$P_D$	$T_A = 25^\circ C$	1.31	W
		$T_A = 70^\circ C$	0.84	W
Storage Temperature Range	$T_{STG}$	-55 to 150	$^\circ C$	
Operating Junction Temperature Range	$T_J$	-40 to 105	$^\circ C$	



## 5. Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>DS</sub> =-250μA	-20			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-20V, V <sub>GS</sub> =0V			1	μA
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>GS</sub> =±12V, V <sub>DS</sub> =0V			±100	nA
<b>ON CHARACTERISTIC</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>DS</sub> =-250μA	-0.4	-0.7	-1	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-4.1A		28	35	mΩ
		V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-3A		38	53	mΩ
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-10V, V <sub>GS</sub> =0V, f=1MHz		830		pF
Output Capacitance	C <sub>oss</sub>			132		pF
Reverse Transfer Capacitance	C <sub>rss</sub>			85		pF
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =-10V, I <sub>D</sub> =-2A, V <sub>GS</sub> =-4.5V		8.8		nC
Gate-Source Charge	Q <sub>gs</sub>			1.4		nC
Gate-Drain("Miller") Charge	Q <sub>gd</sub>			1.9		nC
<b>SWITCHING CHARACTERISTICS</b>						
Turn-On Delay Time	t <sub>D(on)</sub>	V <sub>DD</sub> =-10V, I <sub>D</sub> =-3.3A R <sub>G</sub> =1Ω, V <sub>GEN</sub> =-4.5A		10		ns
Rise Time	t <sub>r</sub>			32		ns
Turn-Off Delay Time	t <sub>D(off)</sub>			50		ns
Fall Time	t <sub>f</sub>			51		ns
Maximum Continuous Drain to Source Diode Forward Current	I <sub>S</sub>				-5	A
Maximum Pulsed Drain to Source Diode Forward Current	I <sub>SM</sub>				-16	A
Drain to Source Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =-4.1A			-1.2	V

Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.

2. Pulse Test: Pulse Width≤300μs, Duty Cycle ≤ 2%.



## 6.1 Typical Characteristics

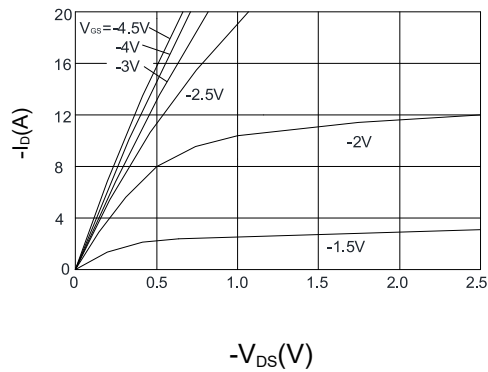


Figure 1: Output Characteristics

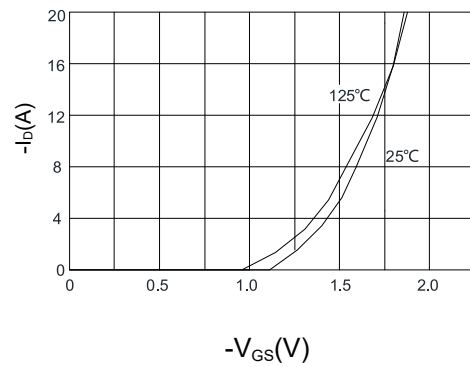


Figure 2: Typical Transfer Characteristics

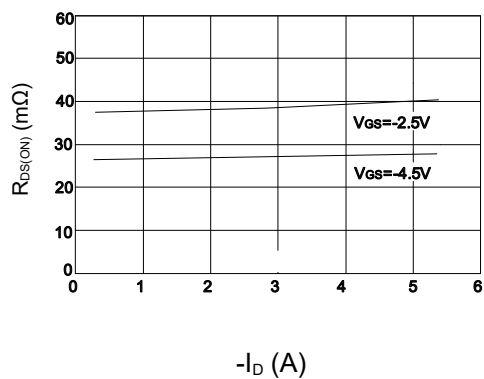


Figure 3: On-resistance vs. Drain Current

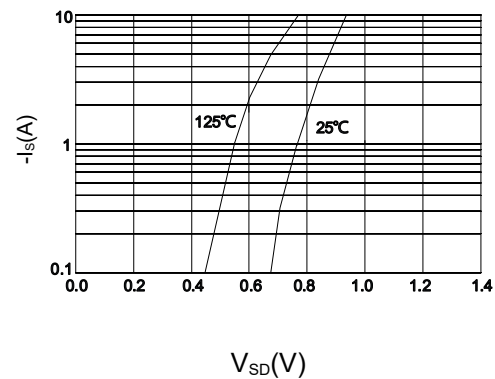


Figure 4: Body Diode Characteristics

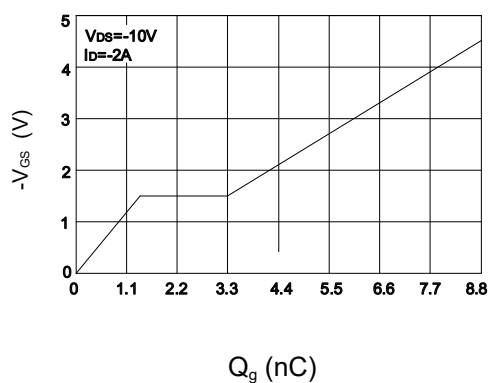


Figure 5: Gate Charge Characteristics

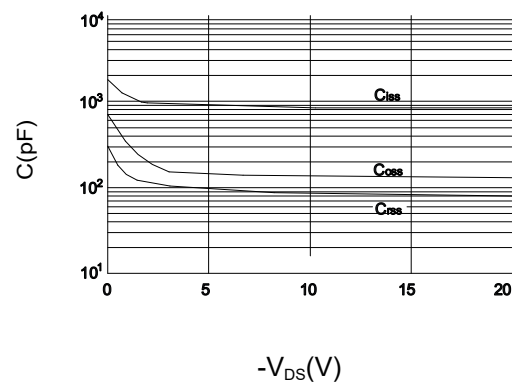
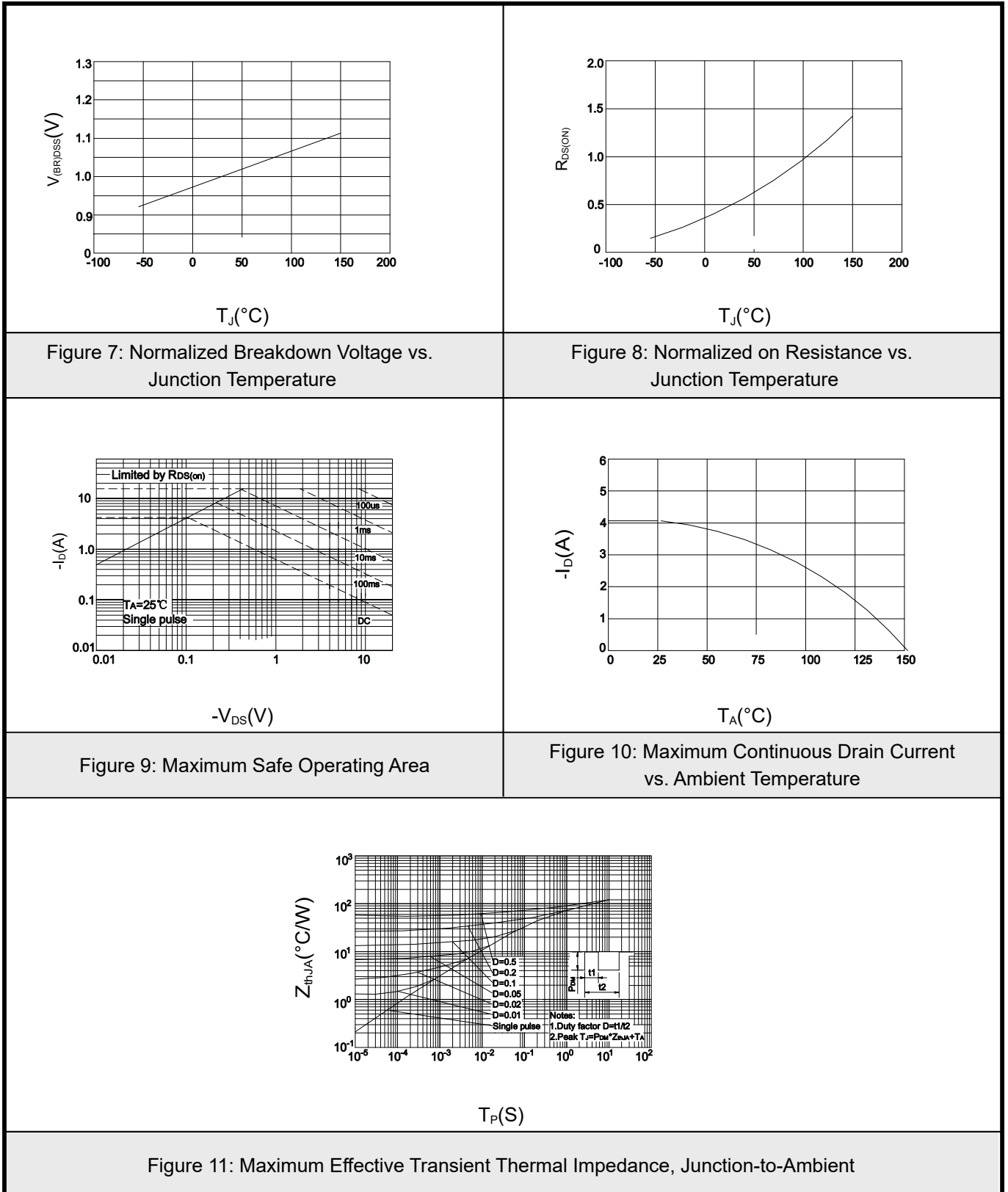


Figure 6: Capacitance Characteristics

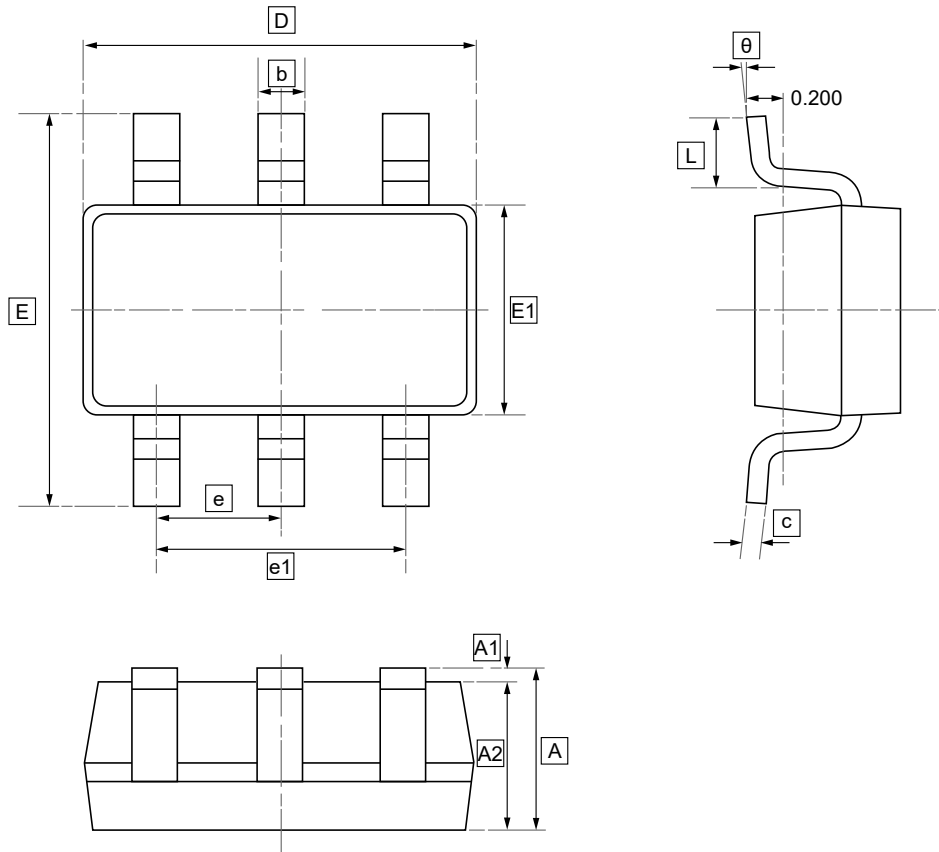


## 6.2 Typical Characteristics





## 7.SOT23-6 Package Outline Dimensions

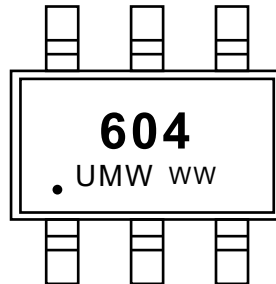


### DIMENSIONS (mm are the original dimensions)

Symbol	A	A1	A2	b	c	D	E1	E	e	e1	L	θ
Min	1.050	0.000	1.050	0.300	0.100	2.820	1.500	2.650	0.950	1.800	0.300	0°
Max	1.250	0.100	1.150	0.500	0.200	3.020	1.700	2.950	BSC	2.000	0.600	8°



## 8. Ordering information



ww: Week Code

Order Code	Package	Base QTY	Delivery Mode
UMW FDC604P	SOT23-6	3000	Tape and reel



## **10.Disclaimer**

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